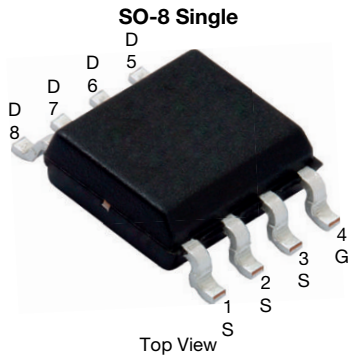


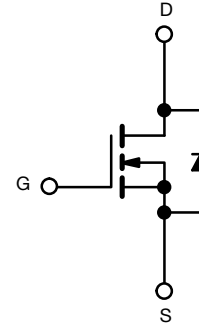
Automotive N-Channel 150 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE


N-Channel MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	150
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.085
I _D (A)	19
Configuration	Single
Package	SO-8

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	150	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	T _C = 25 °C	I _D	18	A
	T _C = 125 °C		10	
Continuous Source Current (Diode Conduction)		I _S	6.5	
Pulsed Drain Current ^a		I _{DM}	72	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	
Single Pulse Avalanche Energy		E _{AS}	20	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	7.1	W
	T _C = 125 °C		2.4	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	85	°C/W
Junction-to-Foot (Drain)		R _{thJF}	25	

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).



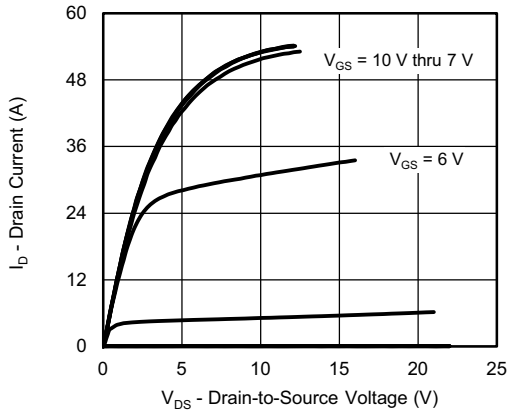
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3	4	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.070	0.085	Ω
		V _{GS} = 10 V	I _D = 10 A, T _C = 125 °C	-	-	0.167	
		V _{GS} = 10 V	I _D = 10 A, T _C = 175 °C	-	-	0.220	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A		-	51	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 75 V, f = 1 MHz	-	1100	1590	pF
Output Capacitance	C _{oss}			-	75	130	
Reverse Transfer Capacitance	C _{rss}			-	33	55	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 75 V, I _D = 5 A	-	25	33	nC
Gate-Source Charge ^c	Q _{gs}			-	5.2	-	
Gate-Drain Charge ^c	Q _{gd}			-	8.7	-	
Gate Resistance	R _g	f = 1 MHz		0.2	0.4	1	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 20 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω		-	11.4	15	ns
Rise Time ^c	t _r			-	3.2	4.5	
Turn-Off Delay Time ^c	t _{d(off)}			-	19.1	25	
Fall Time ^c	t _f			-	2.5	3.2	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	72	A
Forward Voltage	V _{SD}	I _F = 3.5 A, V _{GS} = 0		-	0.75	1.1	V

Notes

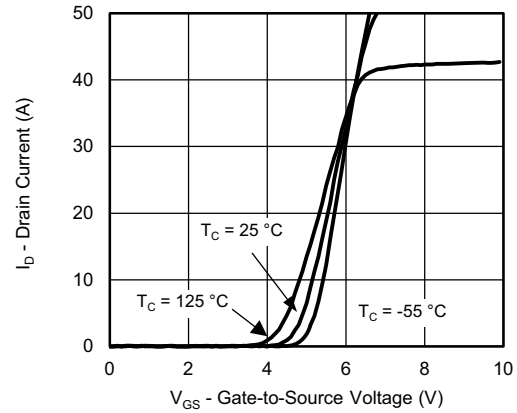
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

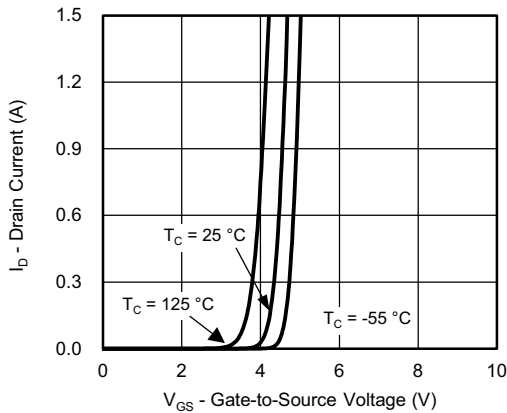
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



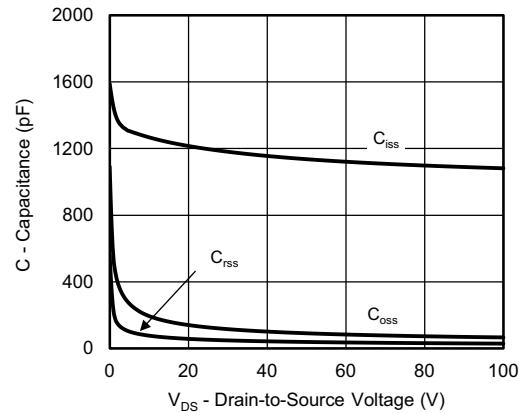
Output Characteristics



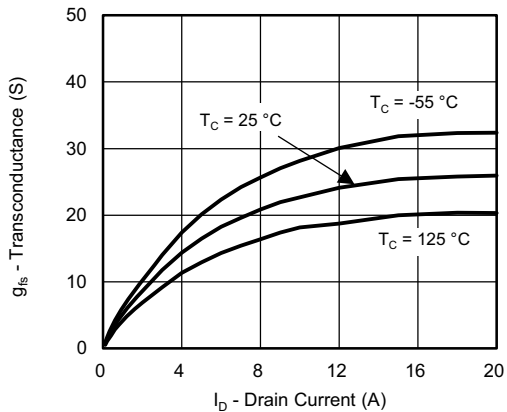
Transfer Characteristics



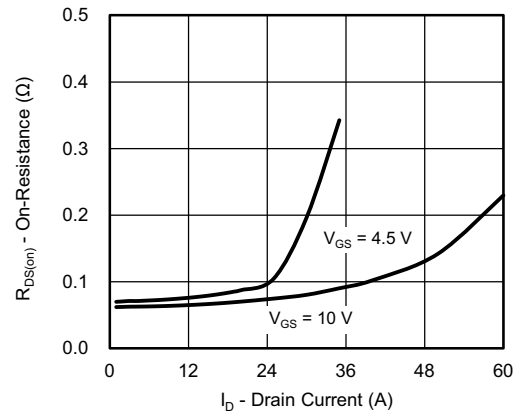
Transfer Characteristics



Capacitance



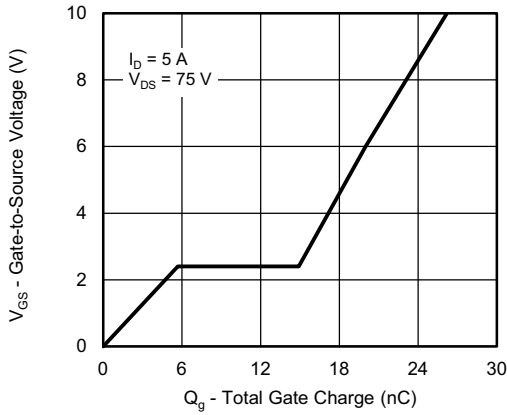
Transconductance



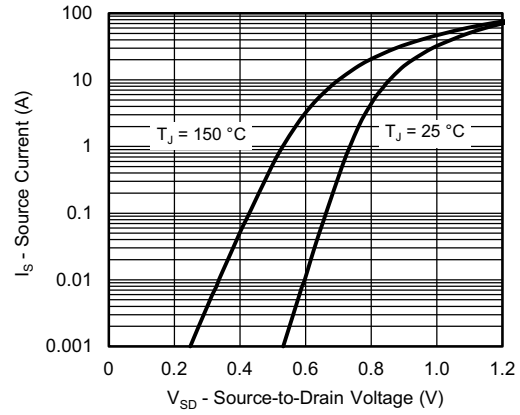
On-Resistance vs. Drain Current



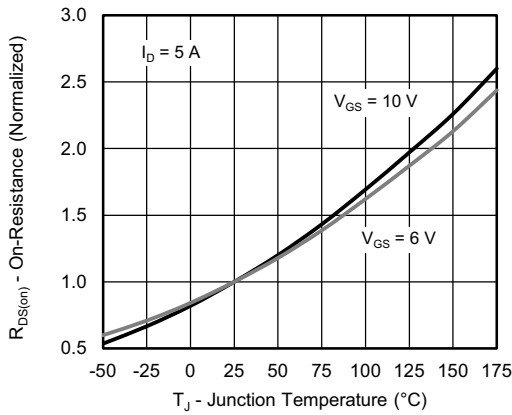
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



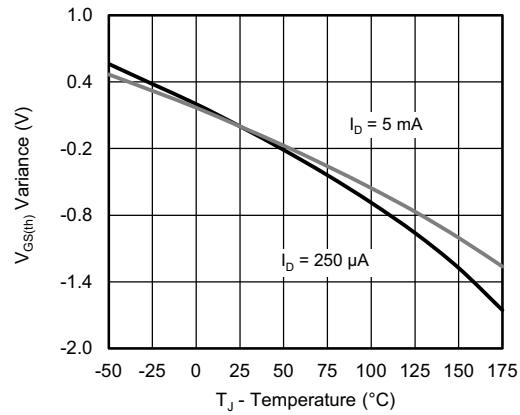
Gate Charge



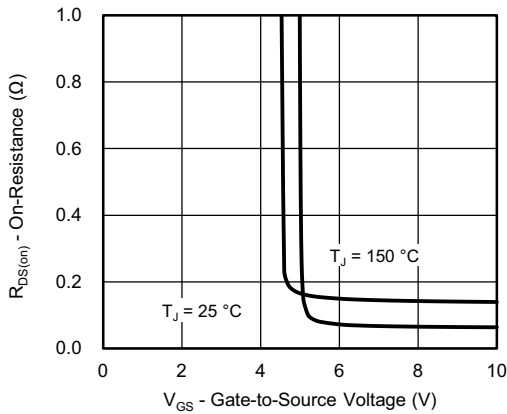
Source Drain Diode Forward Voltage



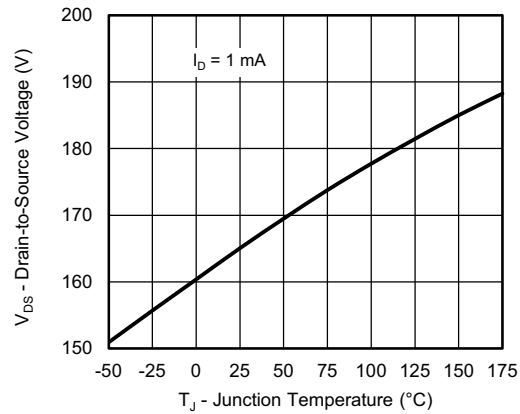
On-Resistance vs. Junction Temperature



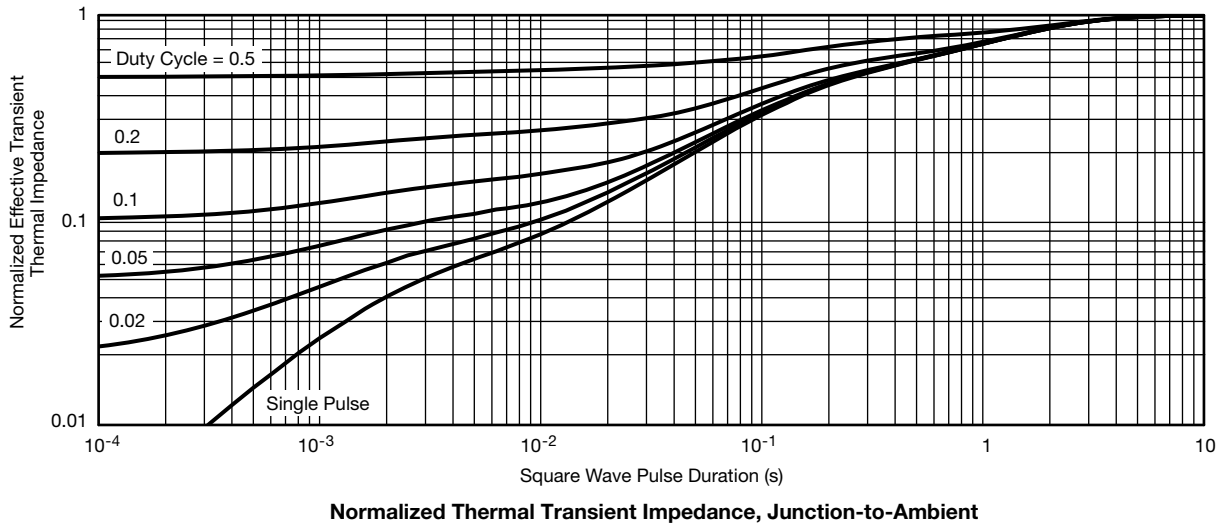
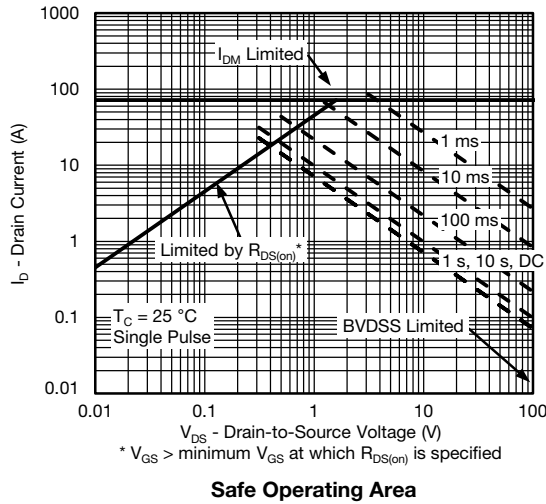
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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